

PATENT ABSTRACTS OF JAPAN

(11)Publication number : 05-102189  
(43)Date of publication of application : 23.04.1993

(51)Int.Cl. H01L 21/336  
H01L 29/784  
C23C 14/26  
C30B 25/14  
H01L 21/205

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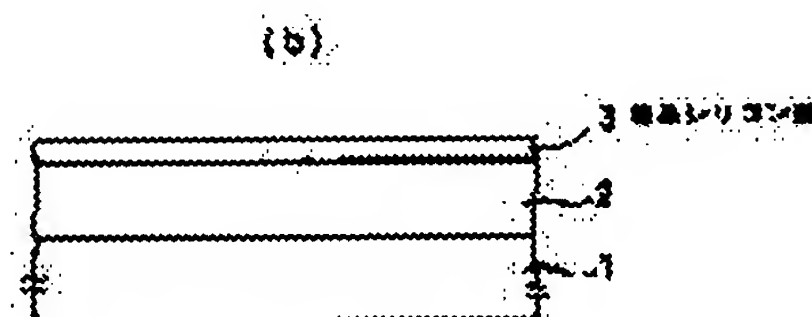
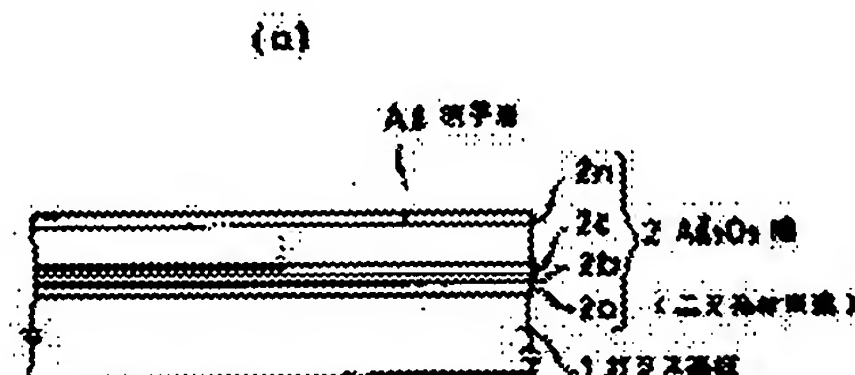
(30)Priority  
Priority number : 03202088 Priority date : 13.08.1991 Priority country : JP

(54) FORMATION METHOD OF THIN FILM, SILICON THIN FILM AND FORMATION METHOD OF SILICON THIN-FILM TRANSISTOR

(57)Abstract:

PURPOSE: To obtain a silicon thin film whose crystallinity at a low temperature is good by a method wherein a binary material film is grown on a substrate and, in succession, the silicon film is grown on the binary material film by an atomic-layer deposition method wherein the substrate is exposed alternately to two atmospheres which separately contain individual atoms constituting a binary material.

CONSTITUTION: By using an atomic-layer deposition method wherein a substrate 1 is exposed alternately to two atmospheres which contain individual atoms constituting a binary material, a binary material film 2 is grown on the substrate 1, and, in succession, a silicon film 3 is grown on the binary material film 2. Thereby, it is possible to obtain the silicon film whose crystallinity is good.



LEGAL STATUS

[Date of request for examination] 10.02.1992  
[Date of sending the examiner's decision of rejection] 17.10.1995  
[Kind of final disposal of application other than the examiner's decision of rejection or application converted registration]  
[Date of final disposal for application]  
[Patent number] 2828152  
[Date of registration] 18.09.1998